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(54) Title: MOLECULAR LAYER DEPOSITION LINER FOR 3D NAND

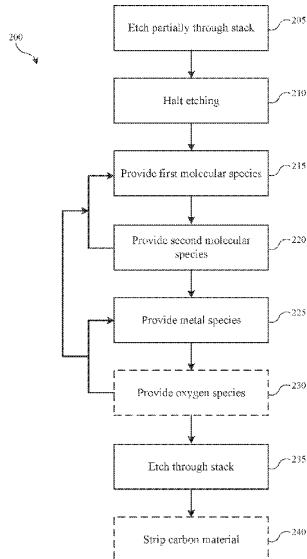


FIG. 2

(57) Abstract: Exemplary methods of semiconductor processing may include etching one or more features partially through a stack of layers formed on a substrate. The methods may include halting the etching prior to penetrating fully through the stack of layers formed on the substrate. The methods may include forming a layer of carbon-containing material along the stack of layers on the substrate. The layer of carbon-containing material may include a metal. The methods may include etching the one or more features fully through the stack of layers on the substrate.

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